Schottky Barrier Diode

NSR0340V2

Schottky barrier diodes are optimized for very low forward voltage drop and low leakage current and are used in a wide range of dc-dc converter, clamping and protection applications in portable devices. NSR0340V2 in a SOD-523 miniature package enables designers to meet the challenging task of achieving higher efficiency and meeting reduced space requirements.

Features

- Very Low Forward Voltage Drop − 410 mV @ 100 mA
- Low Reverse Current − 0.5 μA @ 25 V V_R
- 250 mA of Continuous Forward Current
- Power Dissipation of 200 mW with Minimum Trace
- Very High Switching Speed
- Low Capacitance − C_T = 6 pF
- This is a Pb-Free Device

Typical Applications

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc-dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

Markets

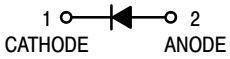
- Mobile Handsets
- MP3 Players
- Digital Camera and Camcorders
- Notebook PCs and PDAs
- GPS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	40	Vdc
Forward Continuous Current (DC)	I_F	250	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	1.0	A
ESD Rating: Human Body Model Machine Model	ESD	Class 2 Class A	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

40 VOLT SCHOTTKY BARRIER DIODE



SOD-523
CASE 502

MARKING DIAGRAM

AD = Device Code
M = Date Code*
▪ = Pb-Free Package
(Note: Microdot may be in either location)

* Date Code orientation position may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NSR0340V2T1G	SOD-523 (Pb-Free)	3000 / Tape & Reel
NSR0340V2T5G	SOD-523 (Pb-Free)	8000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

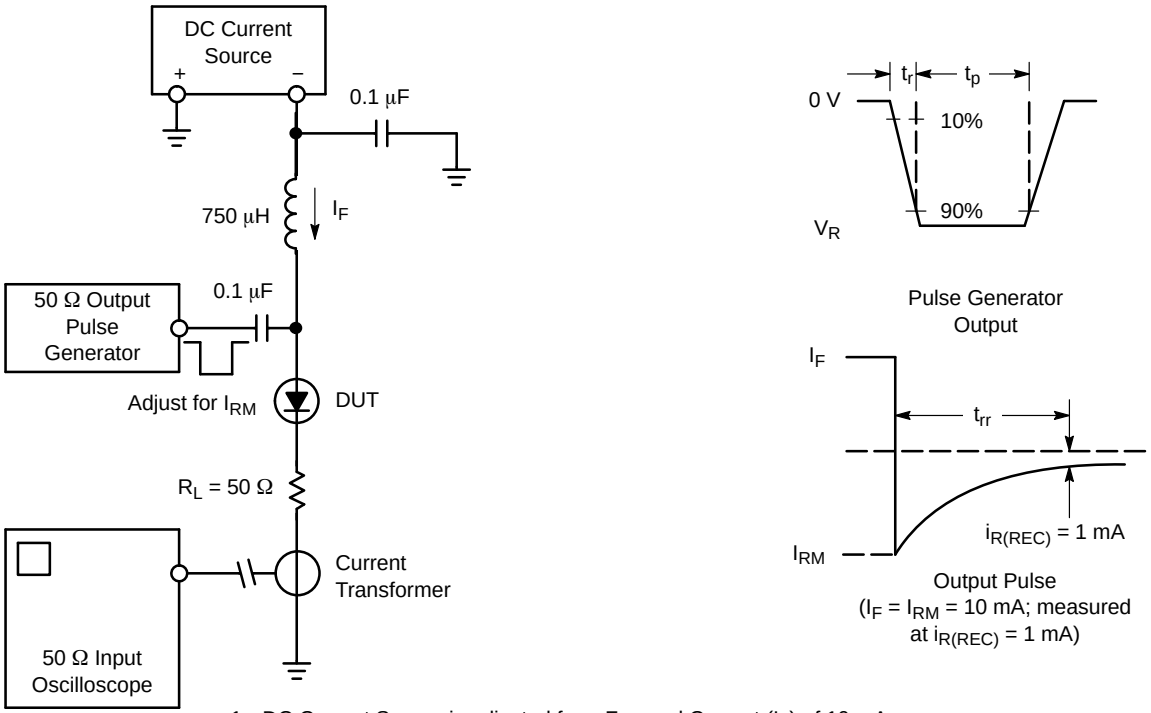
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Ambient (Note 1) Total Power Dissipation @ T_A = 25 °C	 $R_{\theta JA}$ P_D	 600 200	 °C/W mW
Thermal Resistance Junction-to-Ambient (Note 2) Total Power Dissipation @ T_A = 25 °C	 $R_{\theta JA}$ P_D	 300 400	 °C/W mW
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

1. Mounted onto a 4 in square FR-4 board 10 mm sq. 1 oz. Cu 0.06” thick single-sided. Operating to steady state.
2. Mounted onto a 4 in square FR-4 board 1 in sq. 1 oz. Cu 0.06” thick single-sided. Operating to steady state.

ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Leakage (V_R = 10 V) (V_R = 25 V) (V_R = 40 V)	I_R		 0.2 0.5 1.5	 1.0 3.0 6.0	μA
Forward Voltage (I_F = 10 mA) (I_F = 100 mA) (I_F = 200 mA)	V_F		 310 410 470	 350 450 510	mV
Total Capacitance (V_R = 10 V, f = 1 MHz)	C_T		 6.0		pF
Reverse Recovery Time (I_F = I_R = 10 mA, I_R = 1.0 mA)	t_{rr}		 5.0		ns



1. DC Current Source is adjusted for a Forward Current (I_F) of 10 mA.
2. Pulse Generator Output is adjusted for a Peak Reverse Recovery Current I_{RM} of 10 mA.
3. Pulse Generator transition time << t_{rr}.
4. $I_{R(REC)}$ is measured at 1 mA. Typically 0.1 X I_{RM} or 0.25 X I_{RM}.
5. t_p » t_{rr}

Figure 1. Recovery Time Equivalent Test Circuit

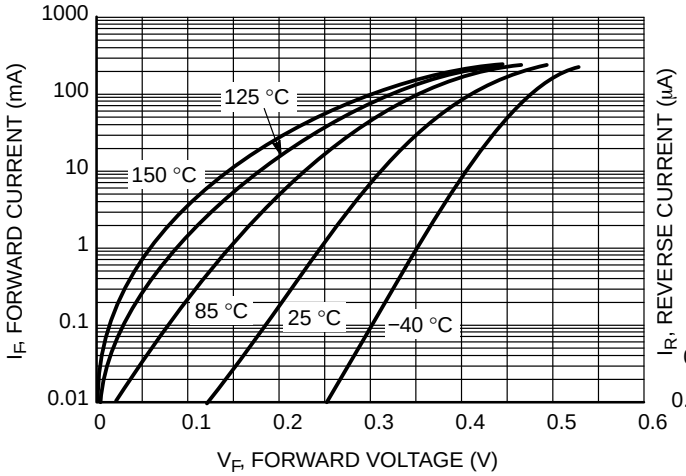


Figure 2. Forward Voltage

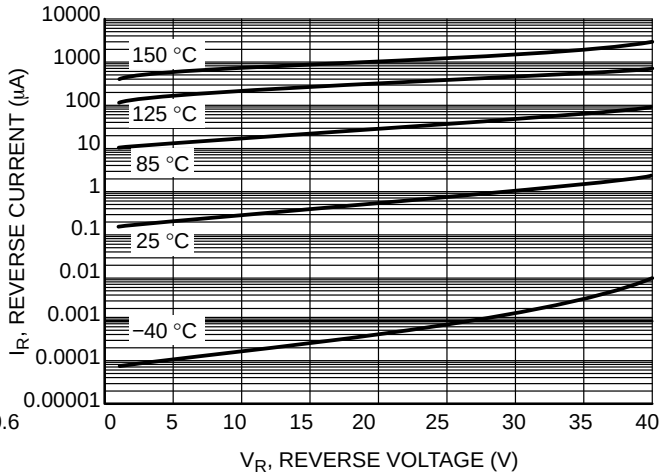


Figure 3. Leakage Current

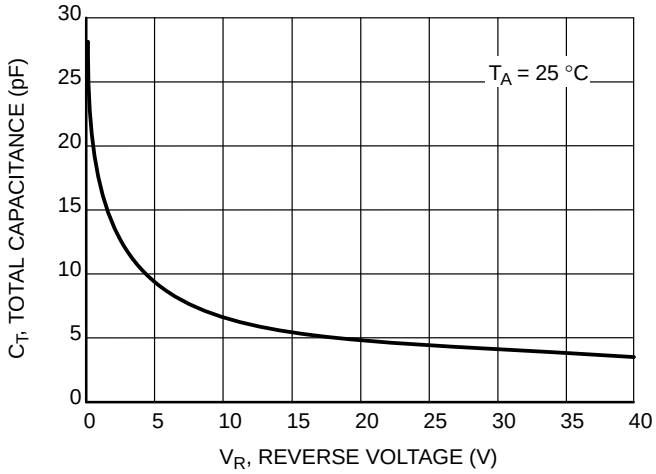
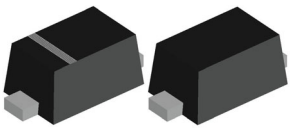


Figure 4. Total Capacitance

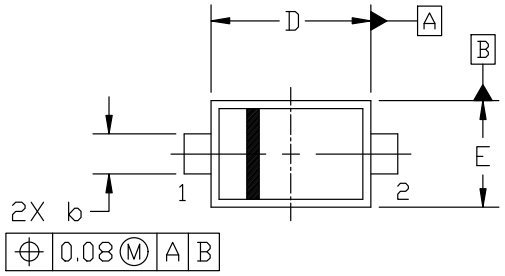
REVISION HISTORY

Revision	Description of Changes	Date
2	Rebranded the Data Sheet to **onsemi** format.	6/16/2025

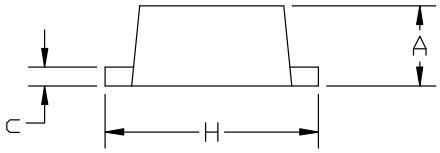


SOD−523 1.20x0.80x0.60
CASE 502
ISSUE F

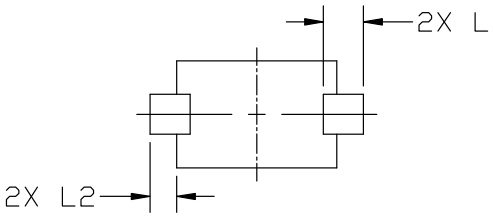
DATE 08 FEB 2024



TOP VIEW



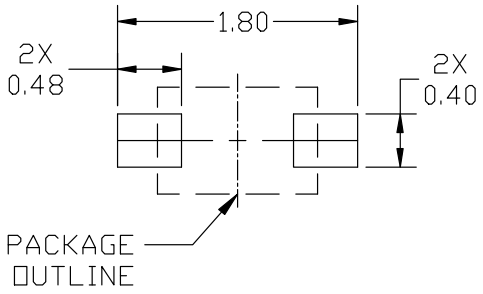
SIDE VIEW



BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

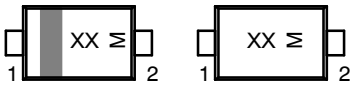
	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	0.50	0.60	0.70
b	0.25	0.30	0.35
c	0.07	0.14	0.20
D	1.10	1.20	1.30
E	0.70	0.80	0.90
H	1.50	1.60	1.70
L	0.30 REF		
L2	0.15	0.20	0.25



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



STYLE 1 STYLE 2

XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. CATHODE (POLARITY BAND)
2. ANODE

STYLE 2:
NO POLARITY

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DESCRIPTION:	**SOD−523 1.20x0.80x0.60**		**PAGE 1 OF 1**

ADDITIONAL INFORMATION

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